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Vishay Siliconix

## Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	0.0085			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.0200			
I <sub>D</sub> (A)	- 30 <sup>a</sup>			
Configuration	Single			

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- ESD Protection: 3000 V
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>q</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

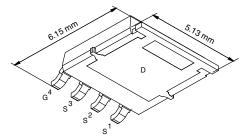
5400 Ω

P-Channel





## PowerPAK® SO-8L Single



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ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ403EEP-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	- 30	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	- 30	
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 30	
Continuous Source Current (Diode Conduct	tion) <sup>a</sup>	I <sub>S</sub>	- 30	Α
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 84	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 50	
Single Pulse Avalanche Energy	L = U. I MIH	E <sub>AS</sub>	125	mJ
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Б	68	10/
	T <sub>C</sub> = 125 °C	$P_{D}$	22	W
Operating Junction and Storage Temperatu	re Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	۰۵
Soldering Recommendations (Peak Temper		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	68	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	2.2	C/VV

#### Notes

- a Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<a href="www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	0 V, I <sub>D</sub> = - 250 μA	- 30	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		- 2.0	- 2.5	V
Cata Cauraa Laakaga	,	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 12 V	-	-	± 2	μΑ
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 1	mA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V	-	-	- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30V, T <sub>J</sub> = 175 °C	-	-	- 250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 30	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10 A	-	0.0070	0.0085	
Dunin Course On State Presistance	В	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10 A, T <sub>J</sub> = 125 °C	-	-	0.0130	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10 A, T <sub>J</sub> = 175 °C	-	-	0.0150	Ω
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 7 A	-	0.0120	0.0200	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> =	- 10 V, I <sub>D</sub> = - 10 A	-	32	-	S
Dynamic <sup>b</sup>							
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 15 V, f = 1 MHz	-	712	890	pF
Total Gate Charge <sup>c</sup>	Qg			-	75	164	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -10 \text{ A}$	-	9.5	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	19	=-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	2	4.3	6.5	kΩ
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	38	57	
Rise Time <sup>c</sup>	t <sub>r</sub>		- 15 V, $R_L$ = 1.5 $\Omega$	ı	82	123	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ - 10 A,	$V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	134	201	115
Fall Time <sup>c</sup>	t <sub>f</sub>			-	178	214	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>					_	
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 84	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	- 3 A, V <sub>GS</sub> = 0 V	-	- 0.75	- 1.2	V

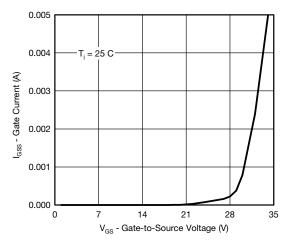
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

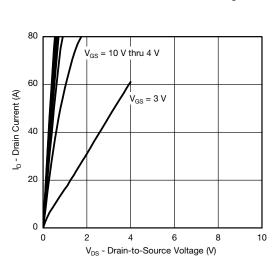
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



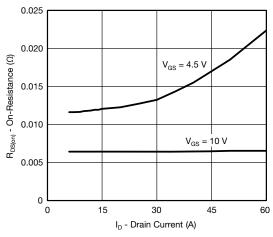
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



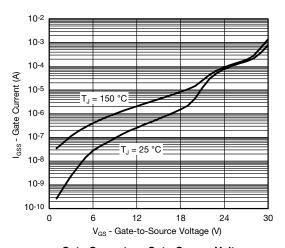
Gate Current vs. Gate-Source Voltage



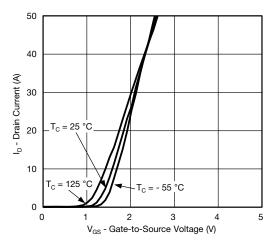
**Output Characteristics** 



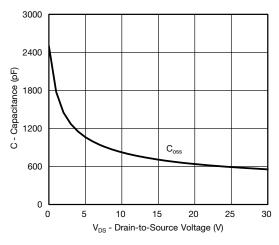
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage



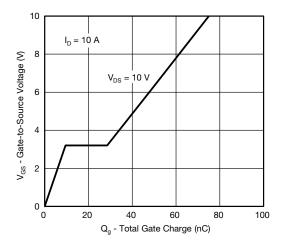
**Transfer Characteristics** 



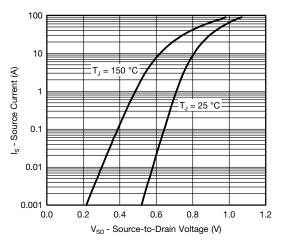
Capacitance



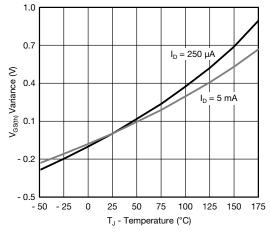
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



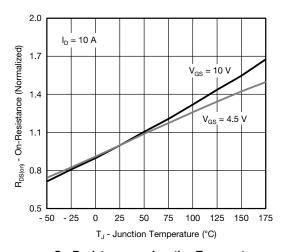
#### **Gate Charge**



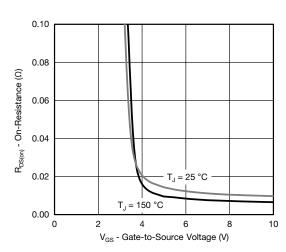
**Source Drain Diode Forward Voltage** 



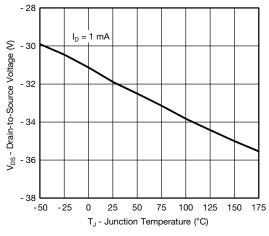
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



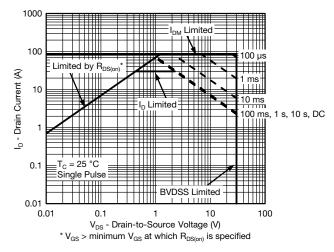
On-Resistance vs. Gate-to-Source Voltage



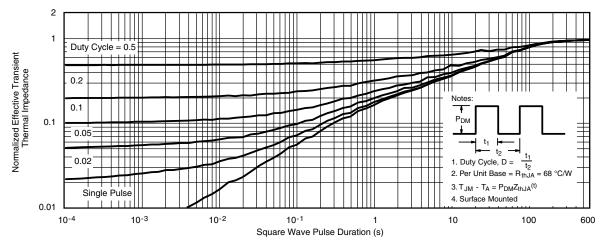
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



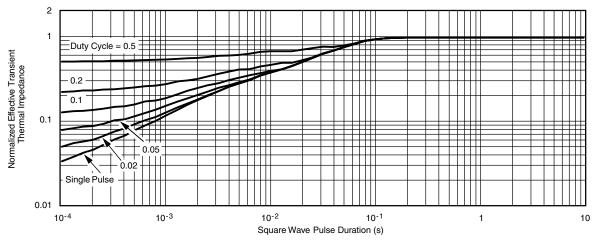
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

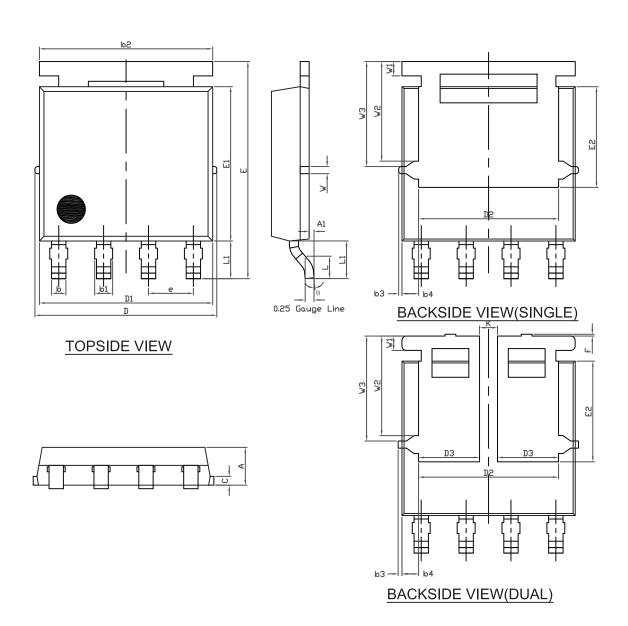
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267076">www.vishay.com/ppg267076</a>.

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# PowerPAK® SO-8L Case Outline



# **Package Information**

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DIM.	MILLIMETERS			INCHES			
DIWI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094		0.004			
b4		0.47		0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е	1.27 BSC			0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2 (for Al product)	2.75	2.85	2.95	0.108	0.112	0.116	
E2 (for other product)	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.51			0.51 0.020			
W	0.23			0.009			
W1	0.41		0.016				
W2	2.82			0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

ECN: C12-0026-Rev. B, 27-Aug-12

DWG: 5976

#### Note

• Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



## **Legal Disclaimer Notice**

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